

Preliminary datasheet

EconoPIM™2 module with TRENCHSTOP™ IGBT7 and emitter controlled 7 diode and NTC

Features

- Electrical features
 - $V_{CES} = 1200\text{ V}$
 - $I_{C\text{ nom}} = 100\text{ A} / I_{CRM} = 200\text{ A}$
 - Low V_{CESat}
 - Overload operation up to 175°C
 - TRENCHSTOP™ IGBT7
- Mechanical features
 - Al_2O_3 substrate with low thermal resistance
 - Copper base plate
 - Integrated NTC temperature sensor
 - PressFIT contact technology



Typical appearance

Potential applications

- Servo drives
- Auxiliary inverters
- Motor drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

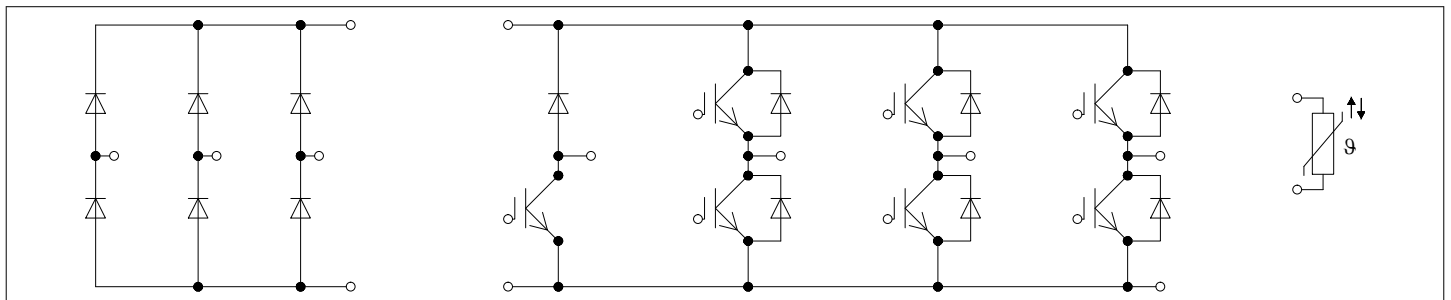


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1 Package

1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	2.5	kV
Material of module baseplate			Cu	
Internal Isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to heatsink	7.5	mm
Comparative tracking index	CTI		> 200	
RTI Elec.	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{SCE}			35		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_C = 25^\circ\text{C}$, per switch		2.5		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25^\circ\text{C}$, per switch		4.3		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting torque for modul mounting	M	- Mounting according to valid application note	M5, Screw	3	6	Nm
Weight	G			180		g

Note: The current under continuous operation is limited to 80A rms in the main AC and DC power terminals and limited to 50A rms per connector pin.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25^\circ\text{C}$	1200	V
Continous DC collector current	I_{CDC}	$T_{vj \max} = 175^\circ\text{C}$ $T_C = 95^\circ\text{C}$	100	A
Repetitive peak collector current	I_{CRM}	$t_p = 1 \text{ ms}$	200	A
Gate-emitter peak voltage	V_{GES}		±20	V

Table 4 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 100\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		1.50	TBD	V
			$T_{vj} = 125\ ^\circ C$		1.64		
			$T_{vj} = 175\ ^\circ C$		1.72		
Gate threshold voltage	V_{GEth}	$I_C = 2.5\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$		5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CE} = 600\ V$			1.8		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$			1.5		Ω
Input capacitance	C_{ies}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			21.7		nF
Reverse transfer capacitance	C_{res}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			0.076		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			0.01	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 100\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 4.3\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.171		μs
			$T_{vj} = 125\ ^\circ C$		0.185		
			$T_{vj} = 175\ ^\circ C$		0.190		
Rise time (inductive load)	t_r	$I_C = 100\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 4.3\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.050		μs
			$T_{vj} = 125\ ^\circ C$		0.055		
			$T_{vj} = 175\ ^\circ C$		0.058		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 100\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 4.3\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.324		μs
			$T_{vj} = 125\ ^\circ C$		0.433		
			$T_{vj} = 175\ ^\circ C$		0.494		
Fall time (inductive load)	t_f	$I_C = 100\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 4.3\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.093		μs
			$T_{vj} = 125\ ^\circ C$		0.183		
			$T_{vj} = 175\ ^\circ C$		0.245		
Turn-on energy loss per pulse	E_{on}	$I_C = 100\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 4.3\ \Omega, di/dt = 1450\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		10.4		mJ
			$T_{vj} = 125\ ^\circ C$		15.3		
			$T_{vj} = 175\ ^\circ C$		17.6		
Turn-off energy loss per pulse	E_{off}	$I_C = 100\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 4.3\ \Omega, dv/dt = 2850\ V/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		6.42		mJ
			$T_{vj} = 125\ ^\circ C$		9.95		
			$T_{vj} = 175\ ^\circ C$		12.3		
SC data	I_{SC}	$V_{GE} \leq 15\ V, V_{CC} = 800\ V, V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$t_P \leq 8\ \mu s, T_{vj} = 150\ ^\circ C$		370		A
			$t_P \leq 7\ \mu s, T_{vj} = 175\ ^\circ C$		350		

3 Diode, Inverter

Table 4 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.371	K/W
Thermal resistance, case to heatsink	R_{thCH}	per IGBT, $\lambda_{grease} = 1 \text{ W/(m}^2\text{K)}$		0.135		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note: $T_{vj\text{ op}} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25^\circ\text{C}$	1200	V
Continuous DC forward current	I_F			100	A
Repetitive peak forward current	I_{FRM}	$t_P = 1 \text{ ms}$		200	A
I^2t - value	I^2t	$t_P = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125^\circ\text{C}$	1000	A^2s
			$T_{vj} = 175^\circ\text{C}$	930	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 100 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^\circ\text{C}$		1.72	TBD
			$T_{vj} = 125^\circ\text{C}$		1.59	
			$T_{vj} = 175^\circ\text{C}$		1.52	
Peak reverse recovery current	I_{RM}	$V_R = 600 \text{ V}, I_F = 100 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 1450 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$	$T_{vj} = 25^\circ\text{C}$		58.2	A
			$T_{vj} = 125^\circ\text{C}$		74.3	
			$T_{vj} = 175^\circ\text{C}$		82.4	
Recovered charge	Q_r	$V_R = 600 \text{ V}, I_F = 100 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 1450 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$	$T_{vj} = 25^\circ\text{C}$		9.83	μC
			$T_{vj} = 125^\circ\text{C}$		15.9	
			$T_{vj} = 175^\circ\text{C}$		20.1	

Table 6 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Reverse recovery energy	E_{rec}	$V_R = 600\text{ V}$, $I_F = 100\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 1450\text{ A}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	3.31		mJ
			$T_{vj} = 125\text{ °C}$	5.01		
			$T_{vj} = 175\text{ °C}$	6.45		
Thermal resistance, junction to case	R_{thJC}	per diode			0.592	K/W
Thermal resistance, case to heatsink	R_{thCH}	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}^*\text{K})$		0.148		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note: $T_{vj\text{ op}} > 150\text{ °C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

4 Diode, Rectifier

Table 7 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25\text{ °C}$		1600	V
Maximum RMS forward current per chip	I_{FRMSM}	$T_C = 110\text{ °C}$		100	A
Maximum RMS current at rectifier output	I_{RMSM}	$T_C = 110\text{ °C}$		100	A
Surge forward current	I_{FSM}	$t_p = 10\text{ ms}$	$T_{vj} = 25\text{ °C}$	745	A
			$T_{vj} = 150\text{ °C}$	515	
I^2t - value	I^2t	$t_p = 10\text{ ms}$	$T_{vj} = 25\text{ °C}$	2780	A ² s
			$T_{vj} = 150\text{ °C}$	1330	

Table 8 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 100\text{ A}$, $T_{vj} = 150\text{ °C}$		1.16		V
Reverse current	I_r	$T_{vj} = 150\text{ °C}$, $V_R = 1600\text{ V}$		1		mA
Thermal resistance, junction to case	R_{thJC}	per diode			0.697	K/W
Thermal resistance, case to heatsink	R_{thCH}	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}^*\text{K})$		0.153		K/W

Table 8 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Temperature under switching conditions	$T_{vj, op}$		-40		150	°C

5 IGBT, Brake-Chopper

Table 9 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25\text{ °C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj\ max} = 175\text{ °C}$ $T_C = 115\text{ °C}$	50	A
Repetitive peak collector current	I_{CRM}	$t_P = 1\text{ ms}$	100	A
Gate-emitter peak voltage	V_{GES}		±20	V

Table 10 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 50\text{ A}$, $V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$	1.50	TBD	V
			$T_{vj} = 125\text{ °C}$	1.64		
			$T_{vj} = 175\text{ °C}$	1.72		
Gate threshold voltage	V_{GEth}	$I_C = 1.28\text{ mA}$, $V_{CE} = V_{GE}$, $T_{vj} = 25\text{ °C}$	5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\text{ V}$, $V_{CE} = 600\text{ V}$		0.92		µC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\text{ °C}$		0		Ω
Input capacitance	C_{ies}	$f = 100\text{ kHz}$, $T_{vj} = 25\text{ °C}$, $V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$		11.1		nF
Reverse transfer capacitance	C_{res}	$f = 100\text{ kHz}$, $T_{vj} = 25\text{ °C}$, $V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$		0.039		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\text{ V}$, $V_{GE} = 0\text{ V}$			0.008	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = 20\text{ V}$, $T_{vj} = 25\text{ °C}$			100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 50\text{ A}$, $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 8.2\text{ Ω}$	$T_{vj} = 25\text{ °C}$	0.060		µs
			$T_{vj} = 125\text{ °C}$	0.062		
			$T_{vj} = 175\text{ °C}$	0.063		
Rise time (inductive load)	t_r	$I_C = 50\text{ A}$, $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 8.2\text{ Ω}$	$T_{vj} = 25\text{ °C}$	0.036		µs
			$T_{vj} = 125\text{ °C}$	0.040		
			$T_{vj} = 175\text{ °C}$	0.042		

Table 10 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-off delay time (inductive load)	t_{doff}	$I_C = 50 \text{ A}$, $V_{\text{CE}} = 600 \text{ V}$, $V_{\text{GE}} = \pm 15 \text{ V}$, $R_{\text{Goff}} = 8.2 \Omega$	$T_{\text{vj}} = 25 \text{ }^\circ\text{C}$	0.290		μs
			$T_{\text{vj}} = 125 \text{ }^\circ\text{C}$	0.380		
			$T_{\text{vj}} = 175 \text{ }^\circ\text{C}$	0.420		
Fall time (inductive load)	t_f	$I_C = 50 \text{ A}$, $V_{\text{CE}} = 600 \text{ V}$, $V_{\text{GE}} = \pm 15 \text{ V}$, $R_{\text{Goff}} = 8.2 \Omega$	$T_{\text{vj}} = 25 \text{ }^\circ\text{C}$	0.110		μs
			$T_{\text{vj}} = 125 \text{ }^\circ\text{C}$	0.200		
			$T_{\text{vj}} = 175 \text{ }^\circ\text{C}$	0.270		
Turn-on energy loss per pulse	E_{on}	$I_C = 50 \text{ A}$, $V_{\text{CE}} = 600 \text{ V}$, $L_\sigma = 35 \text{ nH}$, $V_{\text{GE}} = \pm 15 \text{ V}$, $R_{\text{Gon}} = 8.2 \Omega$, $di/dt = 800 \text{ A}/\mu\text{s}$ ($T_{\text{vj}} = 175 \text{ }^\circ\text{C}$)	$T_{\text{vj}} = 25 \text{ }^\circ\text{C}$	5.35		mJ
			$T_{\text{vj}} = 125 \text{ }^\circ\text{C}$	7.04		
			$T_{\text{vj}} = 175 \text{ }^\circ\text{C}$	8		
Turn-off energy loss per pulse	E_{off}	$I_C = 50 \text{ A}$, $V_{\text{CE}} = 600 \text{ V}$, $L_\sigma = 35 \text{ nH}$, $V_{\text{GE}} = \pm 15 \text{ V}$, $R_{\text{Goff}} = 8.2 \Omega$, $dv/dt = 2900 \text{ V}/\mu\text{s}$ ($T_{\text{vj}} = 175 \text{ }^\circ\text{C}$)	$T_{\text{vj}} = 25 \text{ }^\circ\text{C}$	3.33		mJ
			$T_{\text{vj}} = 125 \text{ }^\circ\text{C}$	5.32		
			$T_{\text{vj}} = 175 \text{ }^\circ\text{C}$	6.58		
SC data	I_{SC}	$V_{\text{GE}} \leq 15 \text{ V}$, $V_{\text{CC}} = 800 \text{ V}$, $V_{\text{CEmax}} = V_{\text{CES}} - L_{\text{sCE}} \cdot di/dt$	$t_P \leq 8 \mu\text{s}$, $T_{\text{vj}} = 150 \text{ }^\circ\text{C}$	190		A
			$t_P \leq 7 \mu\text{s}$, $T_{\text{vj}} = 175 \text{ }^\circ\text{C}$	180		
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.580	K/W
Thermal resistance, case to heatsink	R_{thCH}	per IGBT, $\lambda_{\text{grease}} = 1 \text{ W}/(\text{m}^2\text{K})$		0.147		K/W
Temperature under switching conditions	$T_{\text{vj op}}$		-40		175	$^\circ\text{C}$

Note: $T_{\text{vj op}} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

6 Diode, Brake-Chopper

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{\text{vj}} = 25 \text{ }^\circ\text{C}$	1200	V
Continuous DC forward current	I_F		35	A
Repetitive peak forward current	I_{FRM}	$t_P = 1 \text{ ms}$	70	A

Table 11 Maximum rated values (continued)

Parameter	Symbol	Note or test condition	Values	Unit
I^2t - value	I^2t	$t_p = 10 \text{ ms}$, $V_R = 0 \text{ V}$	$T_{vj} = 150 \text{ °C}$	A^2s
			$T_{vj} = 175 \text{ °C}$	
			125	
			95	

Table 12 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 35 \text{ A}$, $V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$	1.72	TBD	V
			$T_{vj} = 125 \text{ °C}$	1.59		
			$T_{vj} = 175 \text{ °C}$	1.52		
Peak reverse recovery current	I_{RM}	$V_R = 600 \text{ V}$, $I_F = 35 \text{ A}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 700 \text{ A}/\mu\text{s}$ ($T_{vj} = 175 \text{ °C}$)	$T_{vj} = 25 \text{ °C}$	20.1		A
			$T_{vj} = 125 \text{ °C}$	25.9		
			$T_{vj} = 175 \text{ °C}$	29.8		
Recovered charge	Q_r	$V_R = 600 \text{ V}$, $I_F = 35 \text{ A}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 700 \text{ A}/\mu\text{s}$ ($T_{vj} = 175 \text{ °C}$)	$T_{vj} = 25 \text{ °C}$	2.66		μC
			$T_{vj} = 125 \text{ °C}$	4.73		
			$T_{vj} = 175 \text{ °C}$	6.94		
Reverse recovery energy	E_{rec}	$V_R = 600 \text{ V}$, $I_F = 35 \text{ A}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 700 \text{ A}/\mu\text{s}$ ($T_{vj} = 175 \text{ °C}$)	$T_{vj} = 25 \text{ °C}$	0.95		mJ
			$T_{vj} = 125 \text{ °C}$	1.72		
			$T_{vj} = 175 \text{ °C}$	2.38		
Thermal resistance, junction to case	R_{thJC}	per diode			1.11	K/W
Thermal resistance, case to heatsink	R_{thCH}	per diode, $\lambda_{grease} = 1 \text{ W}/(\text{m} \cdot \text{K})$		0.176		K/W
Temperature under switching conditions	$T_{vj \text{ op}}$		-40		175	°C

Note: $T_{vj \text{ op}} > 150 \text{ °C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

7 NTC-Thermistor

Table 13 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25 \text{ °C}$		5		k Ω
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100 \text{ °C}$, $R_{100} = 493 \text{ }\Omega$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25 \text{ °C}$			20	mW

Table 13 **Characteristic values (continued)**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$		3433		K

Note: *Specification according to the valid application note.*

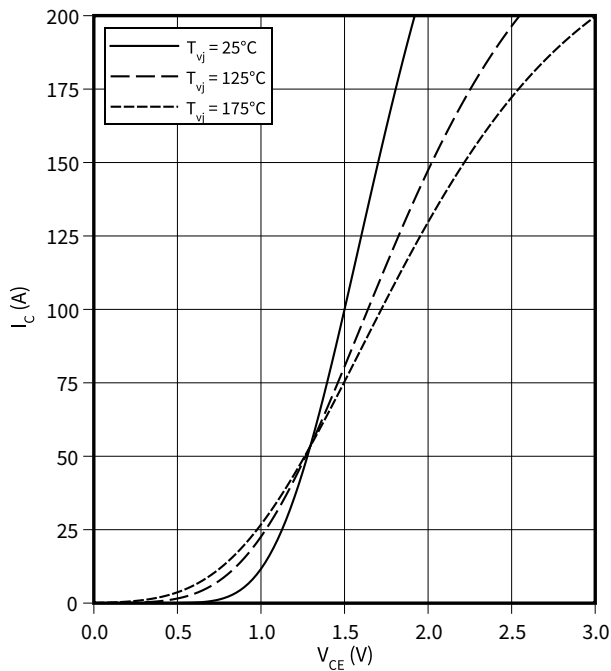
8 Characteristics diagrams

8 Characteristics diagrams

output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

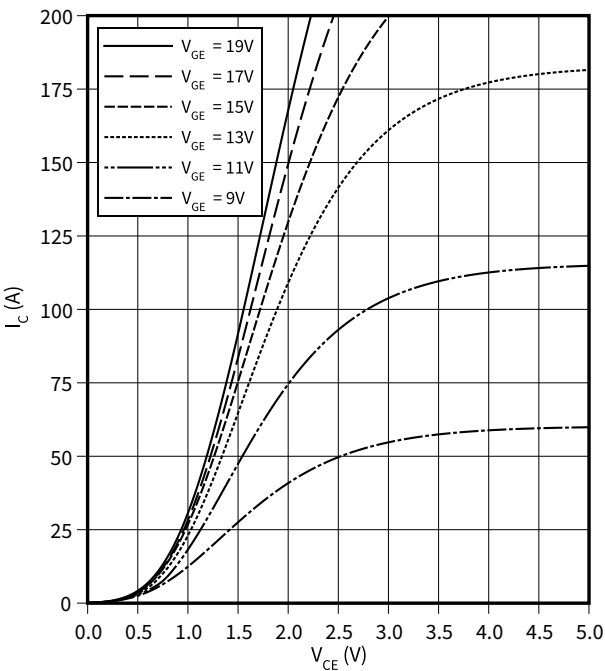
$V_{GE} = 15\text{ V}$



output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

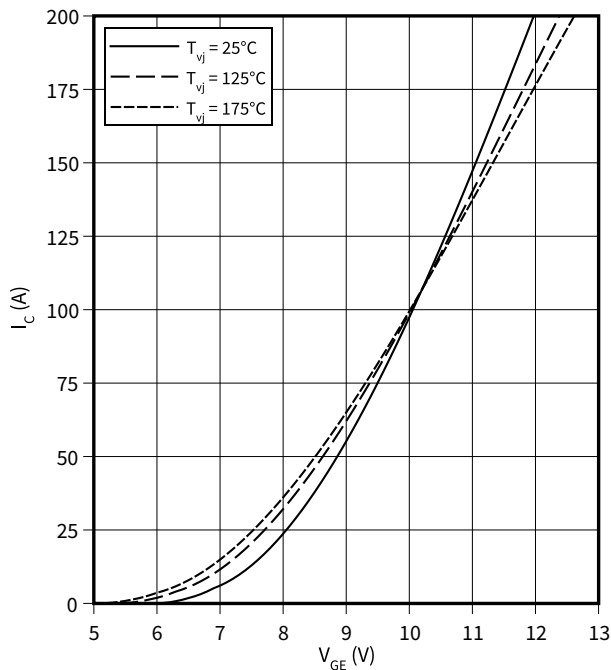
$T_{vj} = 175^\circ\text{C}$



transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$

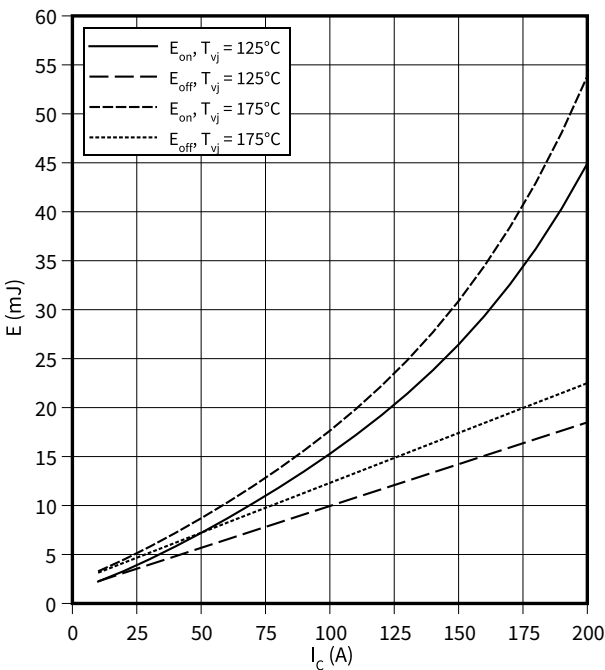
$V_{CE} = 20\text{ V}$



switching losses (typical), IGBT, Inverter

$E = f(I_C)$

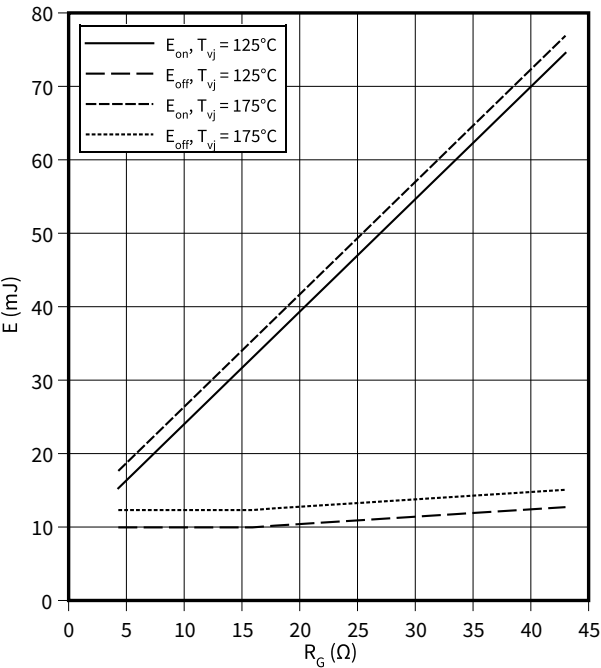
$R_{Goff} = 4.3\ \Omega$, $R_{Gon} = 4.3\ \Omega$, $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$



8 Characteristics diagrams

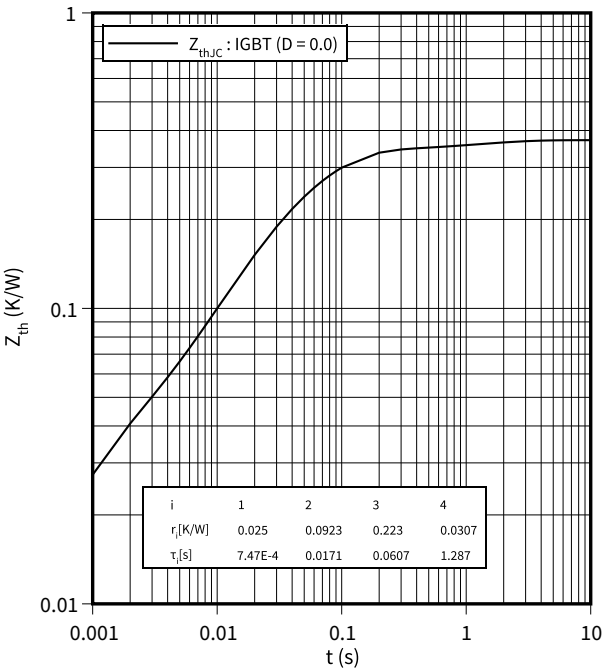
switching losses (typical), IGBT, Inverter

$E = f(R_G)$
 $I_C = 100\text{ A}$, $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$



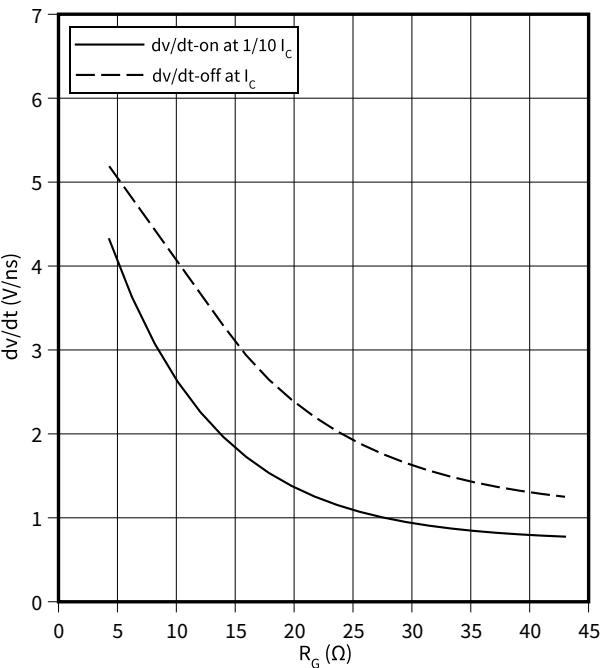
transient thermal impedance , IGBT, Inverter

$Z_{th} = f(t)$



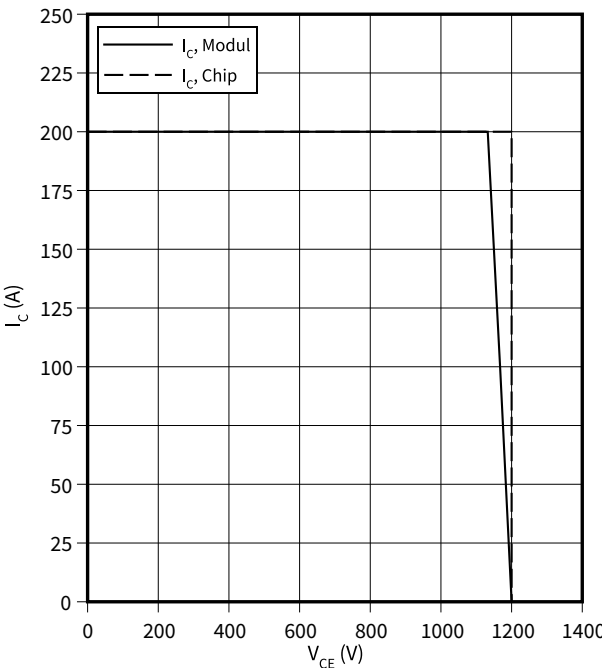
Voltage slope (typical), IGBT, Inverter

$dv/dt = f(R_G)$
 $I_C = 100\text{ A}$, $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 25\text{ }^\circ\text{C}$



reverse bias safe operating area (RBSOA), IGBT, Inverter

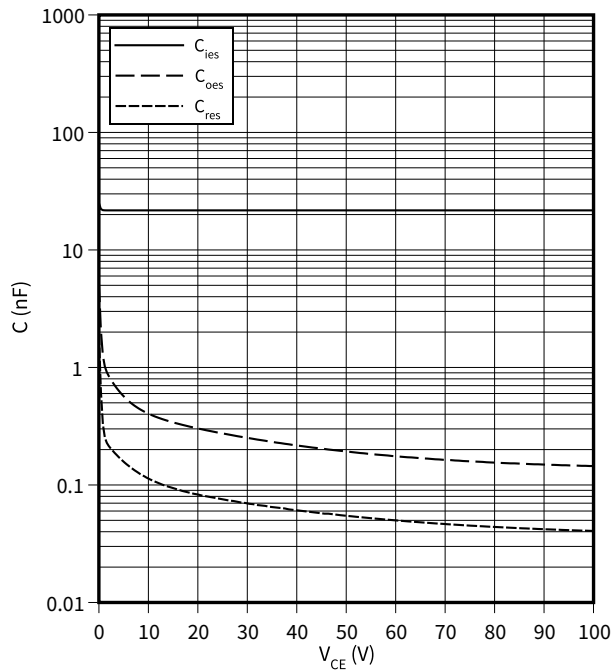
$I_C = f(V_{CE})$
 $R_{Goff} = 4.3\text{ }\Omega$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 175\text{ }^\circ\text{C}$



8 Characteristics diagrams

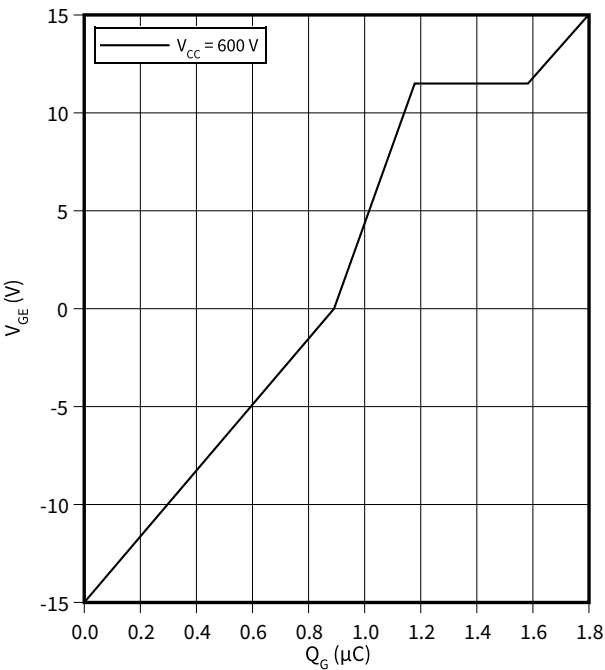
capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$
 $f = 100 \text{ kHz}$, $V_{GE} = 0 \text{ V}$, $T_{vj} = 25 \text{ }^{\circ}\text{C}$



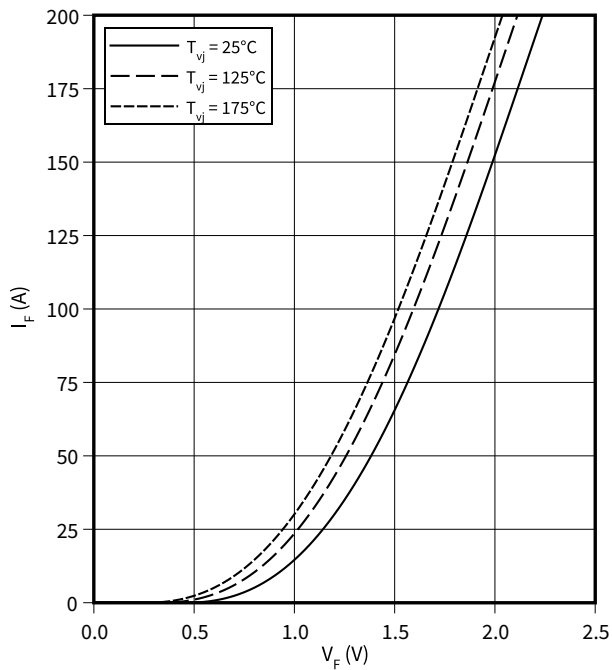
gate charge characteristic (typical), IGBT, Inverter

$V_{GE} = f(Q_G)$
 $I_C = 100 \text{ A}$, $T_{vj} = 25 \text{ }^{\circ}\text{C}$



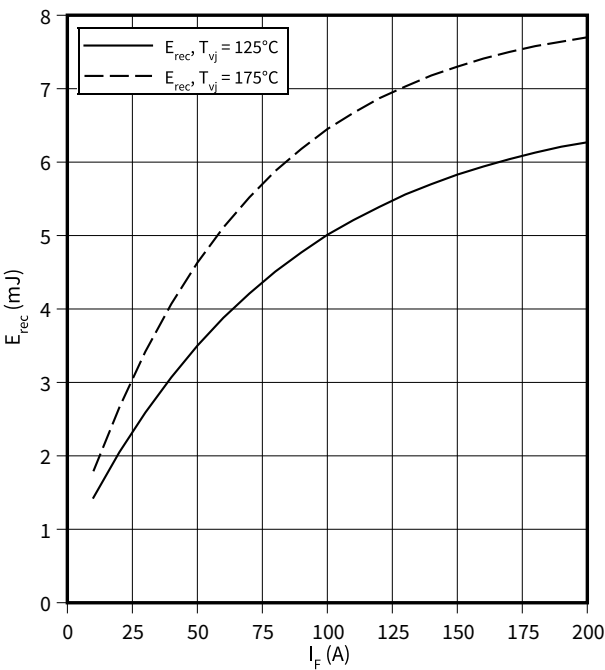
forward characteristic of (typical), Diode, Inverter

$I_F = f(V_F)$



switching losses (typical), Diode, Inverter

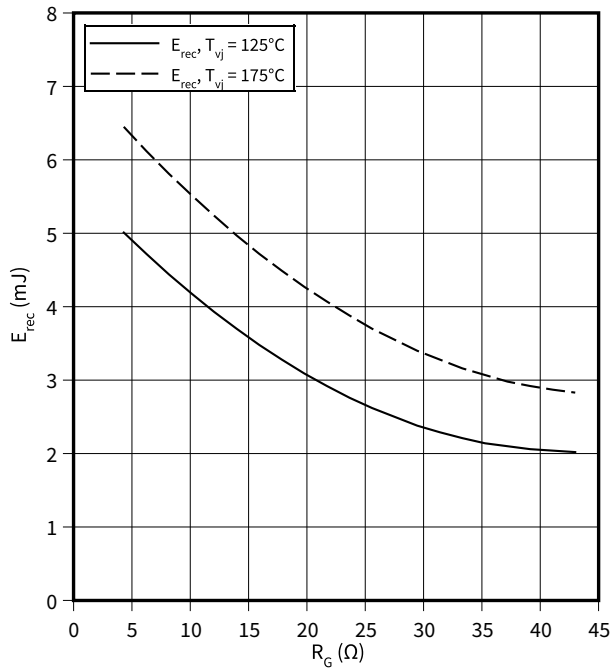
$E_{rec} = f(I_F)$
 $R_{Gon} = 4.3 \text{ } \Omega$, $V_{CE} = 600 \text{ V}$



8 Characteristics diagrams

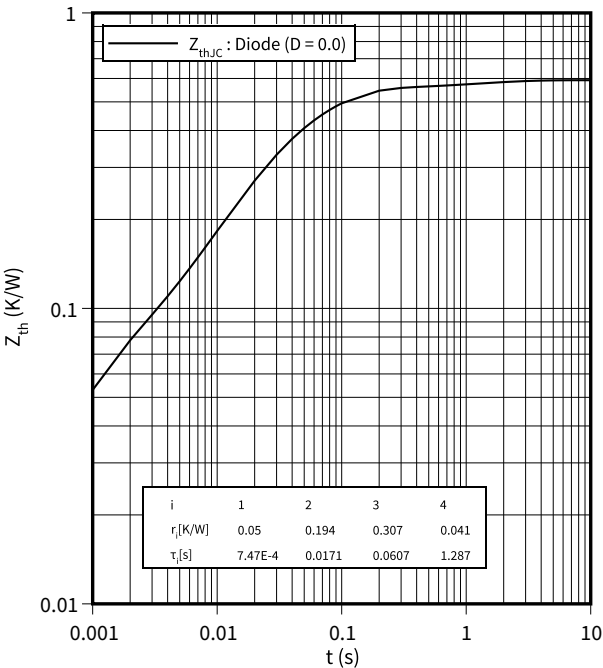
switching losses (typical), Diode, Inverter

$E_{rec} = f(R_G)$
 $V_{CE} = 600\text{ V}, I_F = 100\text{ A}$



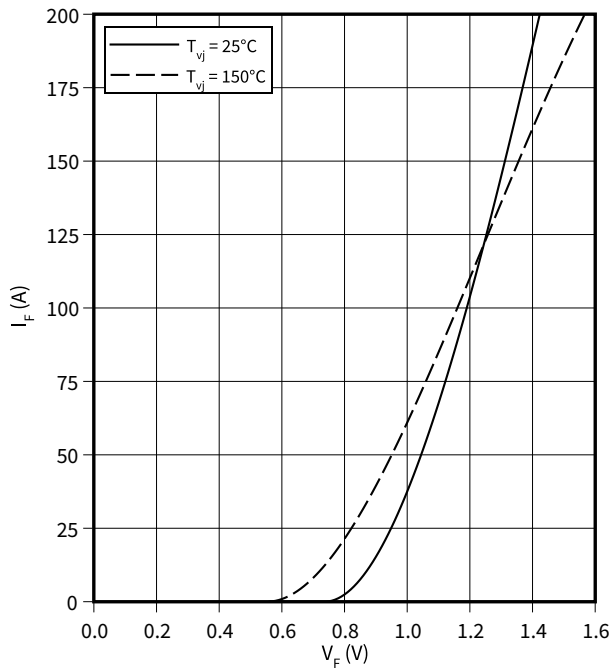
transient thermal impedance , Diode, Inverter

$Z_{th} = f(t)$



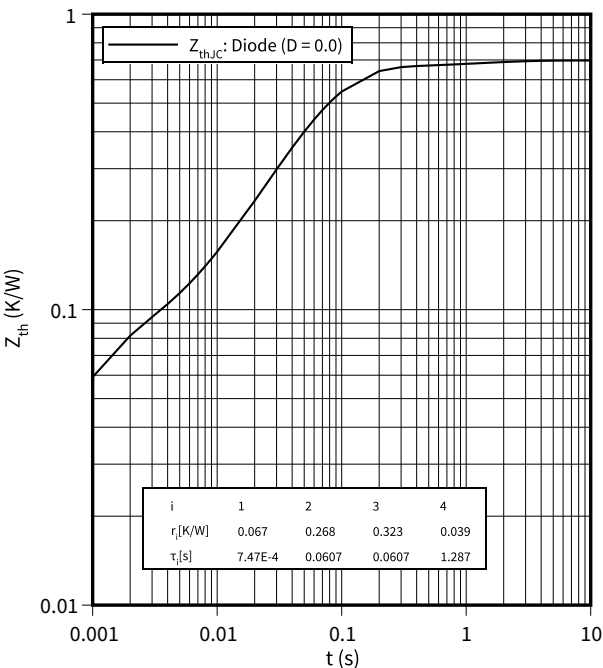
forward characteristic of (typical), Diode, Rectifier

$I_F = f(V_F)$



transient thermal impedance , Diode, Rectifier

$Z_{th} = f(t)$

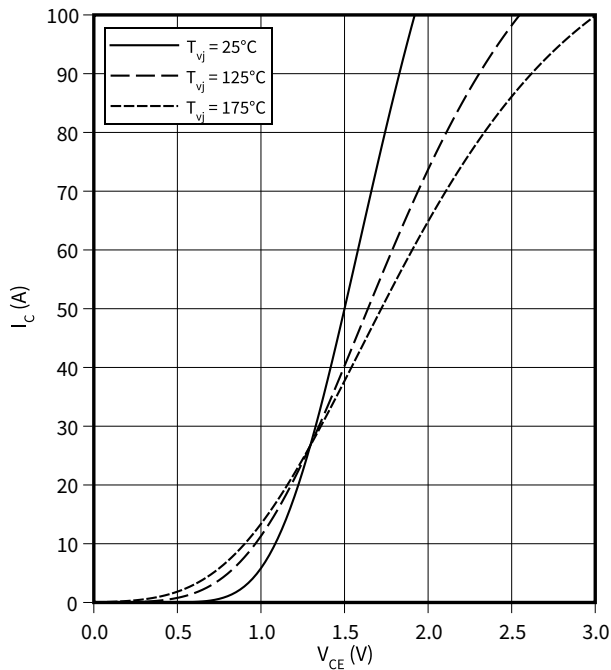


8 Characteristics diagrams

output characteristic (typical), IGBT, Brake-Chopper

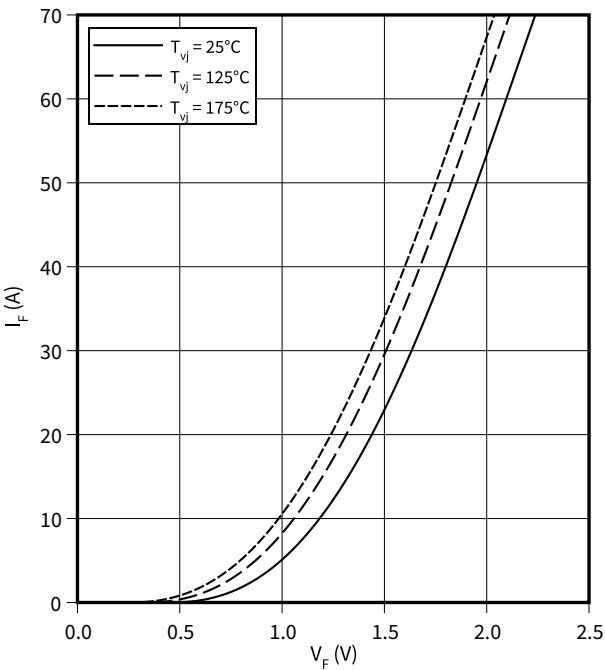
$I_C = f(V_{CE})$

$V_{GE} = 15\text{ V}$



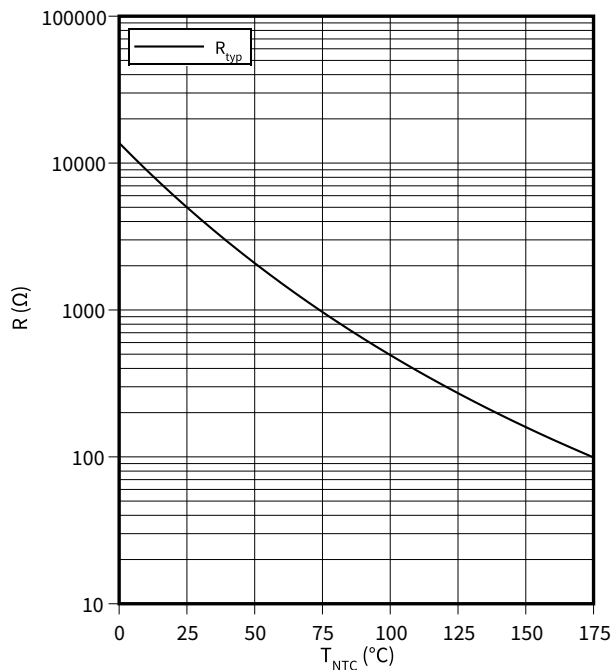
forward characteristic of (typical), Diode, Brake-Chopper

$I_F = f(V_F)$



temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



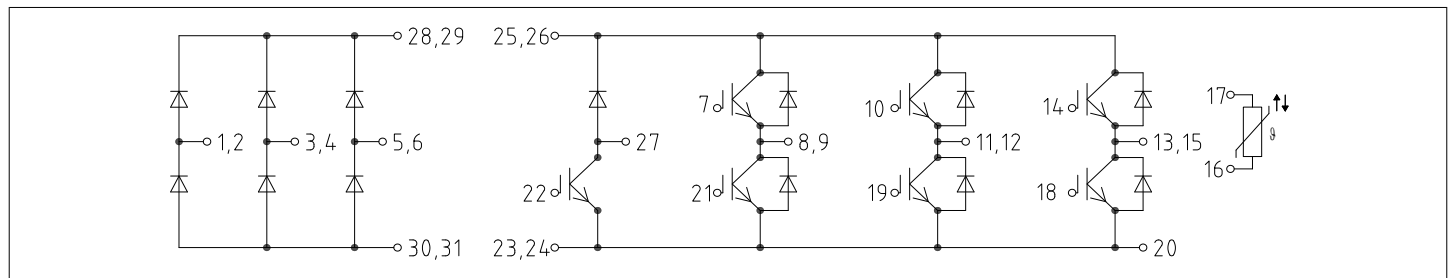


Figure 2

10 Package outlines

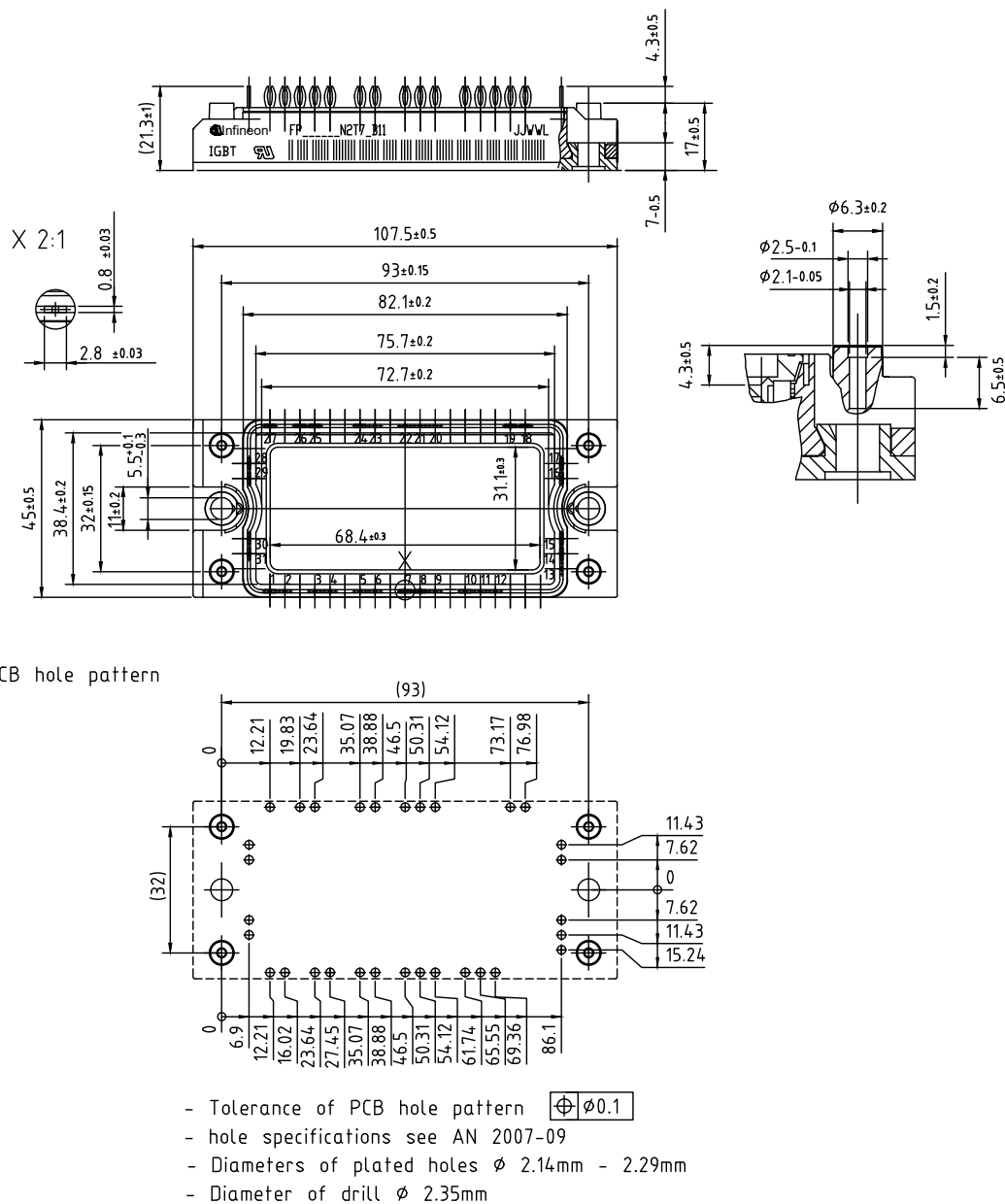


Figure 3

Revision history

Revision history

Document revision	Date of release	Description of changes
0.10	2021-09-21	Initial version

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